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| FORM PTO-1449 | SERIAL NO. 10/667,707 | CASE NO. 9905/35 |
| LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT | FILING DATE September 22, 2003 | GROUP ART UNIT 1765 |
| (use several sheets if necessary) | | APPLICANT(S): Moriceau et al. |

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